

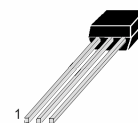
**APPLICATIONS**

Switching Circuit , Interface Circuit.

ABSOLUTE MAXIMUM RATINGS ($T_a=25$)

T_{stg}	Storage Temperature.....	-55~150
T_j	Junction Temperature.....	150
P_C	Collector Dissipation.....	300mW
V_{CBO}	Collector-Base Voltage.....	30V
V_{CEO}	Collector-Emitter Voltage.....	15V
V_{EBO}	Emitter-Base Voltage.....	5V
I_C	Collector Current.....	600mA

TO-92S



- 1 Emitter , E
- 2 Collector,C
- 3 Base , B

ELECTRICAL CHARACTERISTICS ($T_a=25$)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BV_{CBO}	Collector-Base Breakdown Voltage	30			V	$I_C=50 \mu A, I_E=0$
BV_{CEO}	Collector-Emitter Breakdown Voltage	15			V	$I_C=1mA, I_B=0$
BV_{EBO}	Emitter-Base Breakdown Voltage	5			V	$I_E=50 \mu A, I_C=0$
I_{CBO}	Collector Cut-off Current			0.5	μA	$V_{CB}=20V, I_E=0$
I_{EBO}	Emitter Cut-off Current			0.5	μA	$V_{EB}=4V, I_C=0$
H_{FE}	DC Current Gain	100	250	600		$V_{CE}=5V, I_C=50mA$
$V_{CE(sat)}$	Collector- Emitter Saturation Voltage		40	80	mV	$I_C=50mA, I_B=2.5mA$
$V_I (off)$	Input Off Voltage	0.4	0.55	0.8	V	$V_{CE}=5V, I_C=0.1mA$
$V_I (on)$	Input On Voltage	0.6	0.8	1.5	V	$V_{CE}=0.2V, I_C=10mA$
R_I	Input Resistor	1.64	2.2	2.86	K	
f_T	Current Gain-Bandwidth Product		200		MHZ	$V_{CE}=10V, I_C=50mA, f=100MHZ$